

**TrenchT2™ Power  
MOSFET**
**IXTH260N055T2**

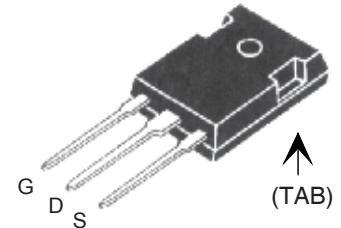
$$V_{DSS} = 55V$$

$$I_{D25} = 260A$$

$$R_{DS(on)} \leq 3.3m\Omega$$

 N-Channel Enhancement Mode  
Avalanche Rated


TO-247


 G = Gate      D = Drain  
S = Source      TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	55	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$	55	V
$V_{GSM}$	Transient	$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	260	A
$I_{LRMS}$	Lead Current Limit, RMS	160	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	780	A
$I_A$	$T_C = 25^\circ\text{C}$	100	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	600	mJ
$P_D$	$T_C = 25^\circ\text{C}$	480	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$T_L$	1.6mm (0.062in.) from case for 10s	300	$^\circ\text{C}$
$T_{sold}$	Plastic body for 10 seconds	260	$^\circ\text{C}$
$M_d$	Mounting torque	1.13 / 10	Nm/lb.in.
<b>Weight</b>		6	g

**Features**

- International standard package
- $175^\circ\text{C}$  Operating Temperature
- High current handling capability
- Avalanche rated
- Low  $R_{DS(on)}$

**Advantages**

- Easy to mount
- Space savings
- High power density

**Applications**

- Automotive
  - Motor Drives
  - 12V Battery
  - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	55		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$			5 $\mu\text{A}$
	$V_{GS} = 0V$ $T_J = 150^\circ\text{C}$			150 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50A$ , Notes 1, 2			3.3 $m\Omega$

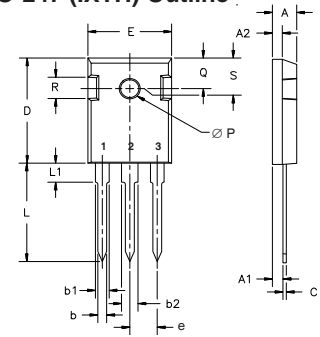
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	55	94	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		10.8	nF
$C_{oss}$			1460	pF
$C_{rss}$			215	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 100\text{A}$ $R_G = 2\Omega$ (External)		20	ns
$t_r$			27	ns
$t_{d(off)}$			36	ns
$t_f$			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		140	nC
$Q_{gs}$			52	nC
$Q_{gd}$			32	nC
$R_{thJC}$			0.31	$^\circ\text{C/W}$
$R_{thCH}$		0.21		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			260 A
$I_{SM}$	Repetitive, Pulse width limited by $T_{JM}$			1000 A
$V_{SD}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 130\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 27\text{V}$		60	ns
$I_{RM}$			3.4	A
$Q_{RM}$			102	nC

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

### TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

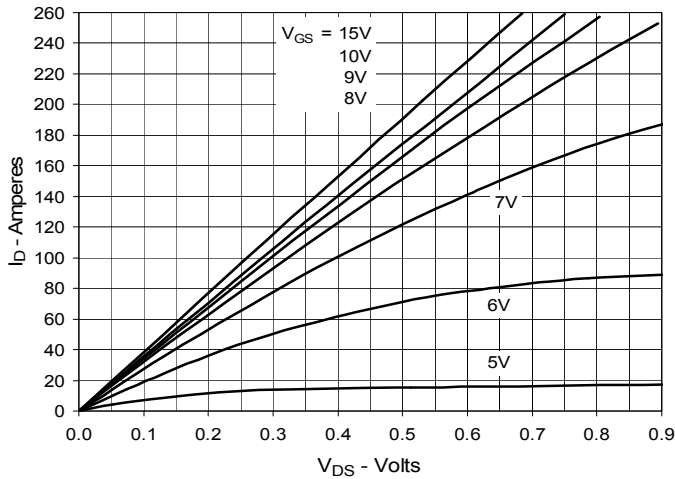
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

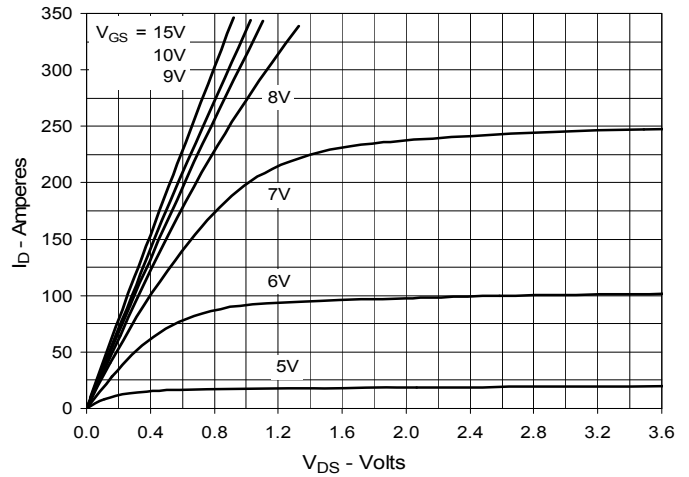
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

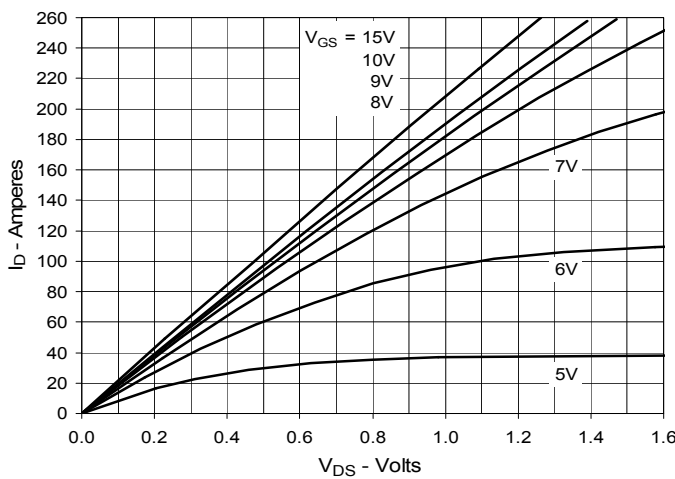
**Fig. 1. Output Characteristics @ 25°C**



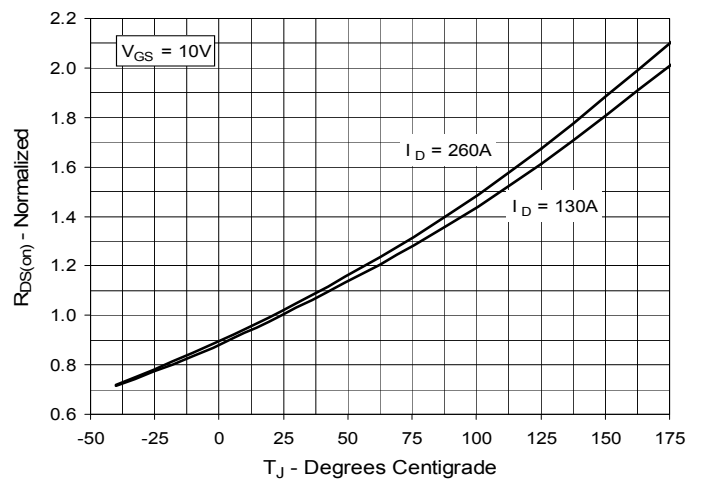
**Fig. 2. Extended Output Characteristics @ 25°C**



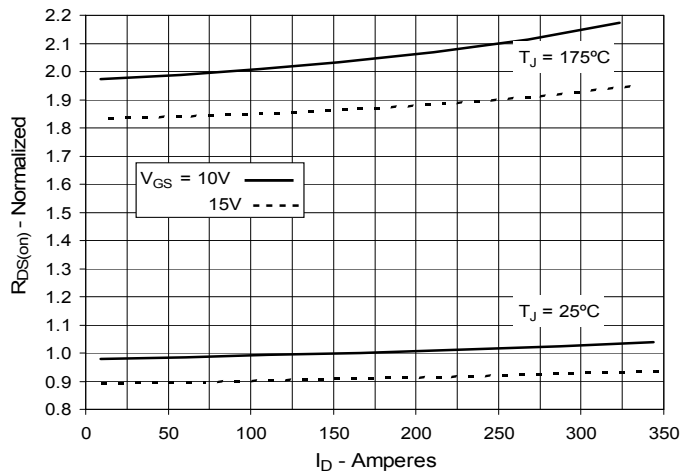
**Fig. 3. Output Characteristics @ 150°C**



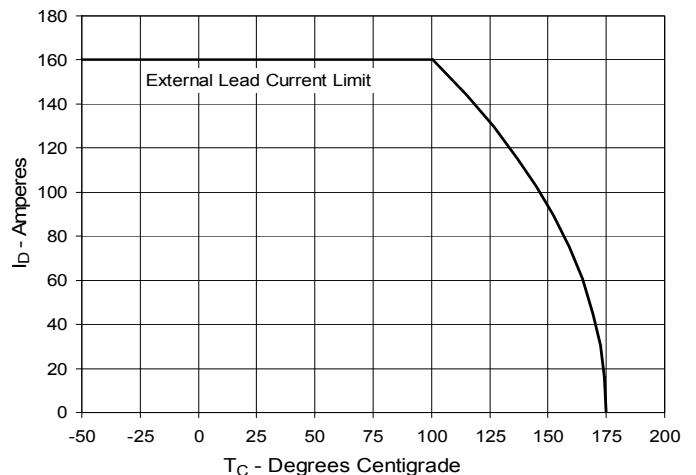
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 130A$  Value vs. Junction Temperature**



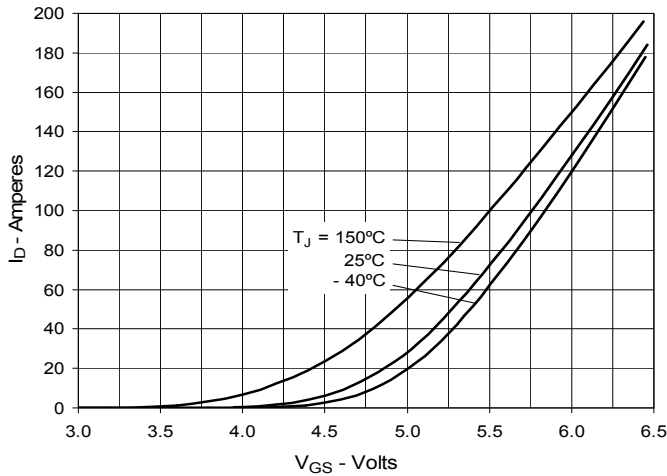
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 130A$  Value vs. Drain Current**



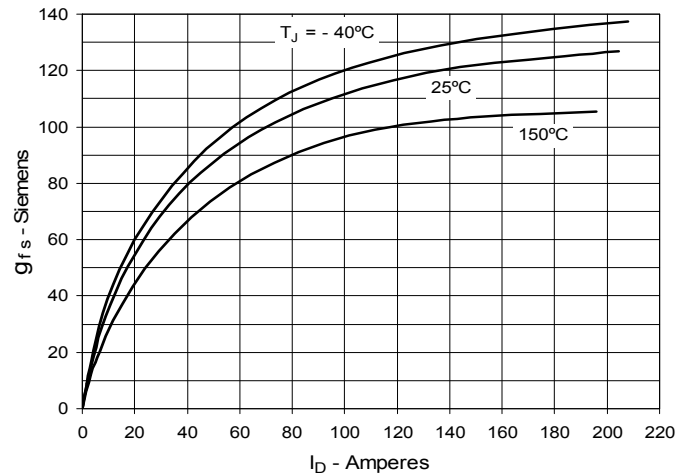
**Fig. 6. Drain Current vs. Case Temperature**



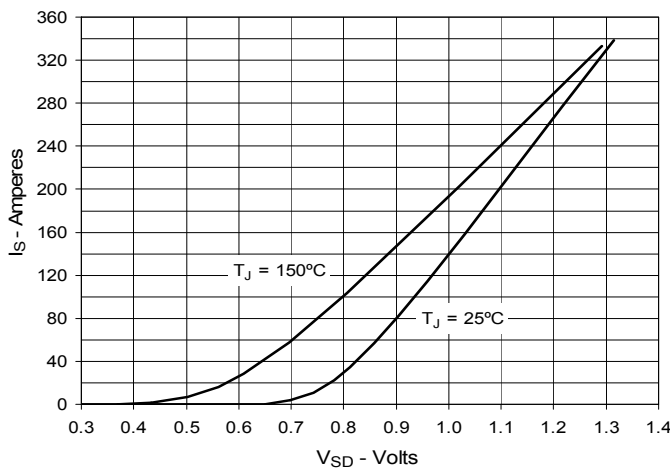
**Fig. 7. Input Admittance**



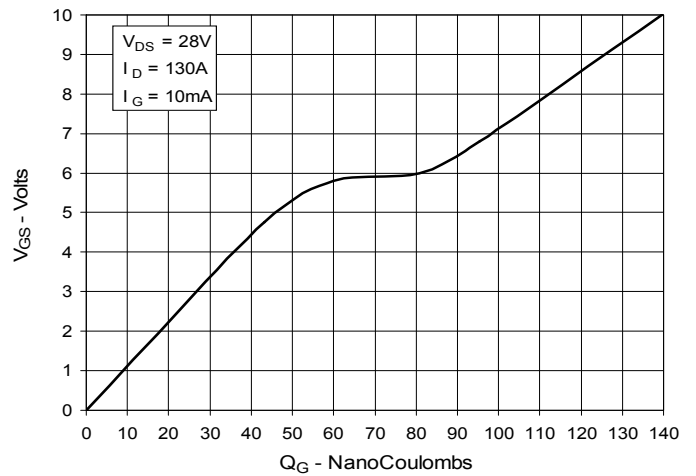
**Fig. 8. Transconductance**



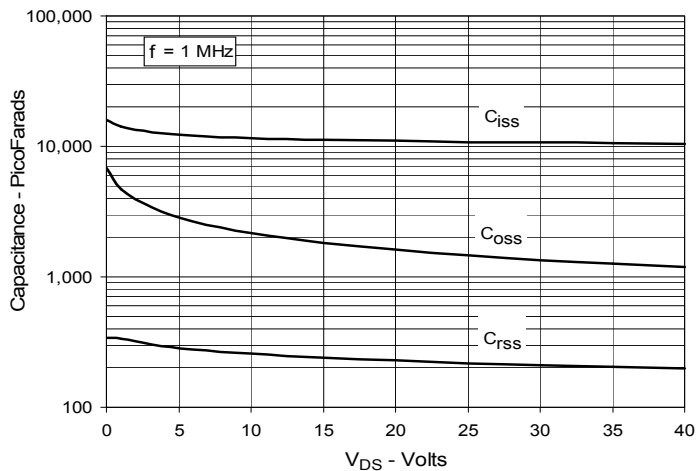
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



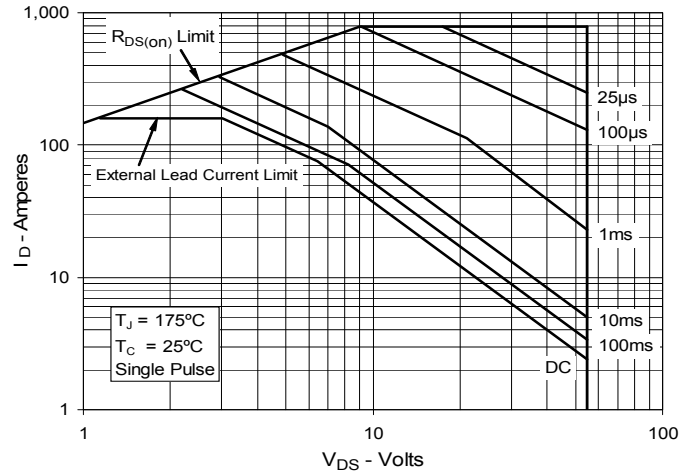
**Fig. 10. Gate Charge**



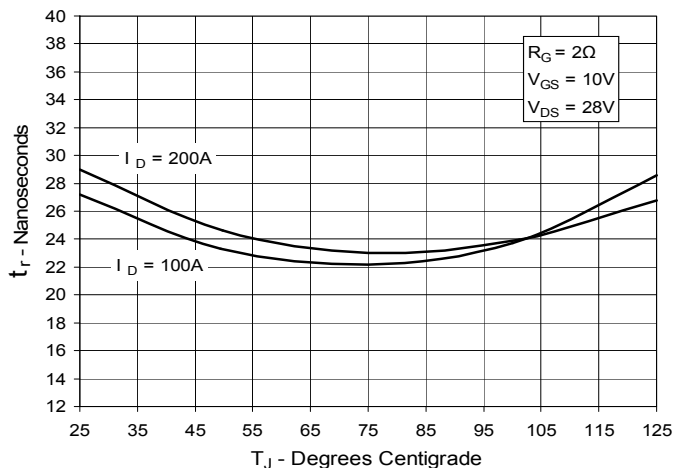
**Fig. 11. Capacitance**



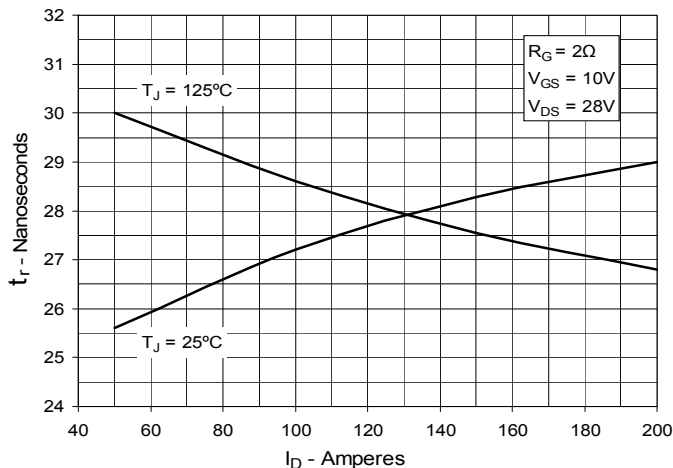
**Fig. 12. Forward-Bias Safe Operating Area**



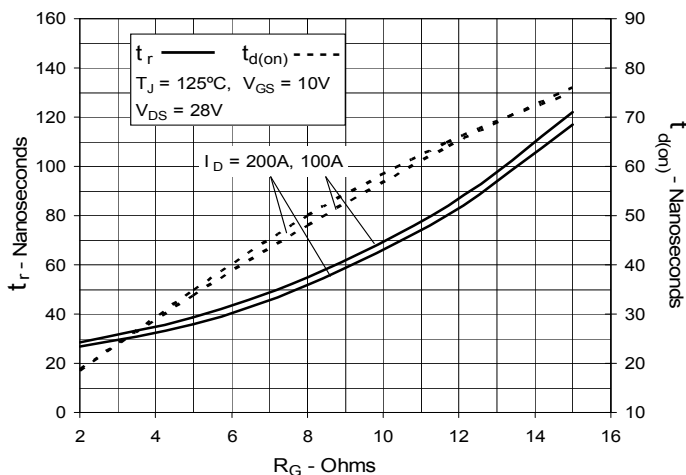
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



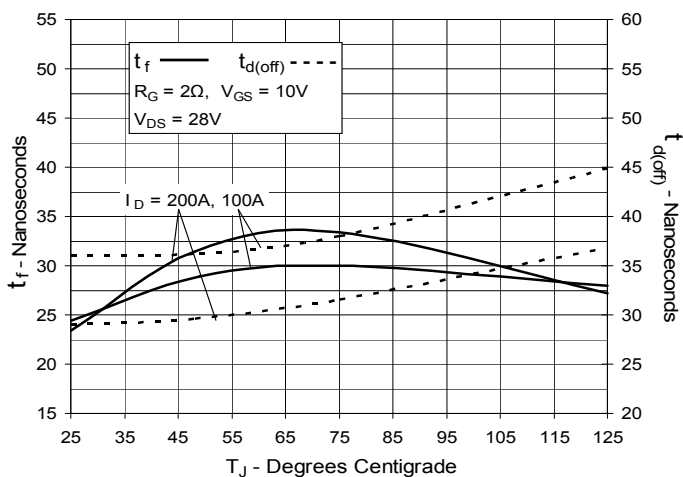
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



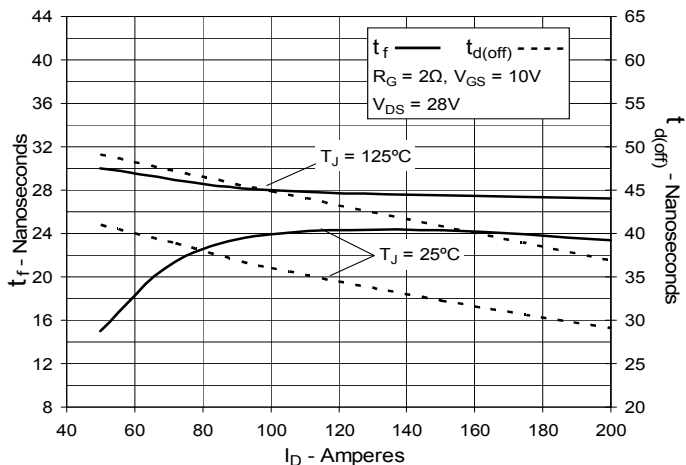
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

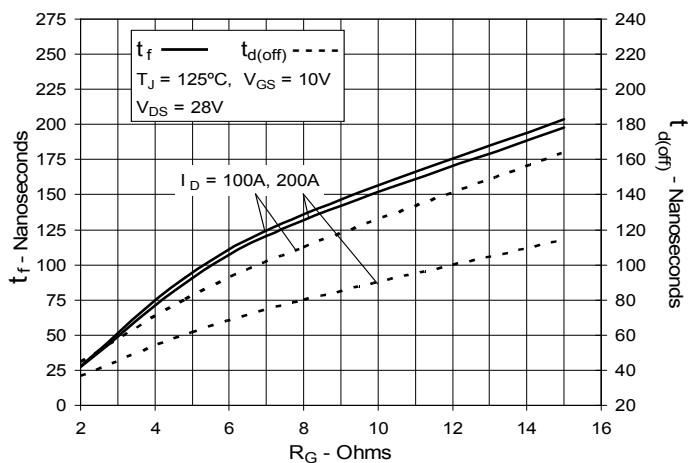


Fig. 19. Maximum Transient Thermal Impedance

